OptiMOS®-P Small-Signal-Transistor

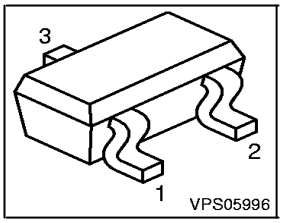
Feature

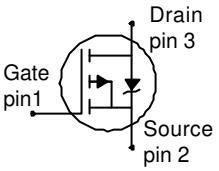
- P-Channel
- Enhancement mode
- Super Logic Level (2.5 V rated)
- 150°C operating temperature
- Avalanche rated
- d*v*/d*t* rated
- Pb-free lead plating; RoHS compliant

Product Summary

V_{DS}	-20	V
$R_{DS(on)}$	1.2	Ω
I_D	-0.39	A

PG-SC-75





Type	Package	Pb-free	Marking
BSA 223SP	PG-SC-75	Yes	BPs

Maximum Ratings, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D		A
T_A=25°C		-0.39	
T_A=70°C		-0.31	
Pulsed drain current	$I_{D\ puls}$	-1.56	
T_A=25°C			
Avalanche energy, single pulse	E_{AS}	1.4	mJ
I_D=-0.39 A , V_{DD}=-10V, R_{GS}=25Ω			
Reverse diode d*v*/d*t*	d*v*/d*t*	-6	kV/µs
I_S=-0.39A, V_{DS}=-16V, d*i*/d*t*=200A/µs, T_{jmax}=150°C			
Gate source voltage	V_{GS}	±12	V
Power dissipation	P_{tot}	0.25	W
T_A=25°C			
Operating and storage temperature	T_j , T_{stg}	-55... +150	°C
IEC climatic category; DIN IEC 68-1		55/150/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point	R_{thJS}	-	-	150	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	500	

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

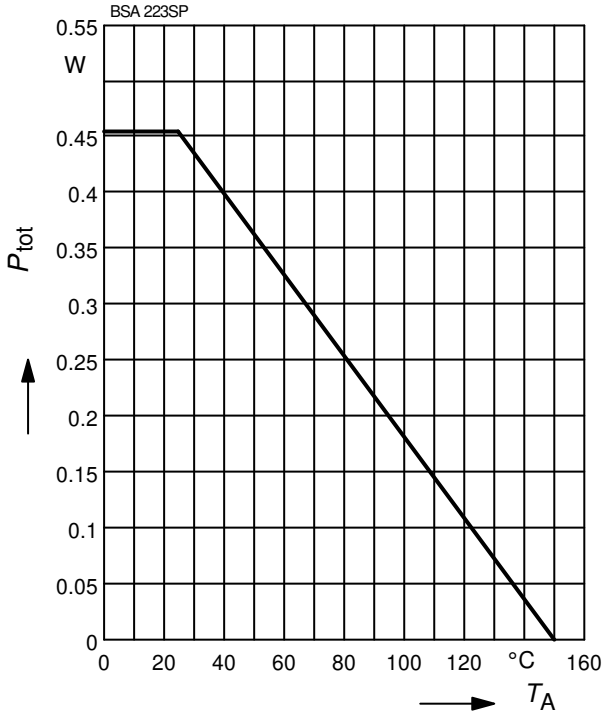
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage V_{GS}=0, I_D=-250µA	$V_{(BR)DSS}$	-20	-	-	V
Gate threshold voltage, V_{GS} = V_{DS} I_D=-1.5µA	$V_{GS(th)}$	-0.6	-0.9	-1.2	
Zero gate voltage drain current	I_{DSS}				µA
V_{DS}=-20V, V_{GS}=0, T_j=25°C		-	-0.1	-1	
V_{DS}=-20V, V_{GS}=0, T_j=150°C		-	-10	-100	
Gate-source leakage current V_{GS}=-12V, V_{DS}=0	I_{GSS}	-	-10	-100	nA
Drain-source on-state resistance V_{GS}=-2.5V, I_D=-0.29A	$R_{DS(on)}$	-	1.27	2.1	Ω
Drain-source on-state resistance V_{GS}=-4.5, I_D=-0.39A	$R_{DS(on)}$	-	0.7	1.2	

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic Characteristics						
Transconductance	g_{fs}	$\lvert V_{DS}\rvert \geq 2 * \lvert I_D\rvert * R_{DS(on)max}$, I_D=-0.31A	0.35	0.7	-	S
Input capacitance	C_{iss}	V_{GS}=0, V_{DS}=-15V, f=1MHz	-	45	56	pF
Output capacitance	C_{oss}		-	21	26	
Reverse transfer capacitance	C_{rss}		-	17	22	
Turn-on delay time	$t_{d(on)}$	V_{DD}=-10V, V_{GS}=-4.5V, I_D=-0.39A, R_G=6Ω	-	3.8	5.7	ns
Rise time	t_r		-	5	7.5	
Turn-off delay time	$t_{d(off)}$		-	5.1	7.6	
Fall time	t_f		-	3.2	4.8	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=-10V, I_D=-0.39A	-	-0.04	-0.05	nC
Gate to drain charge	Q_{gd}		-	-0.4	-0.5	
Gate charge total	Q_g	V_{DD}=-10V, I_D=-0.39A, V_{GS}=0 to -4.5V	-	-0.5	-0.62	
Gate plateau voltage	$V_{(plateau)}$	V_{DD}=-10V, I_D=-0.39A	-	-2.2	-2.7	V
Reverse Diode						
Inverse diode continuous forward current	I_S	T_A=25°C	-	-	-0.39	A
Inv. diode direct current, pulsed	I_{SM}		-	-	-1.56	
Inverse diode forward voltage	V_{SD}	V_{GS}=0, I_F=-0.39	-	-1	-1.33	V
Reverse recovery time	t_{rr}	V_R=-10V, $\lvert I_F\rvert = \lvert I_D\rvert$, di_F/dt=100A/µs	-	7.6	9.5	ns
Reverse recovery charge	Q_{rr}		-	1.1	1.4	nC

1 Power dissipation

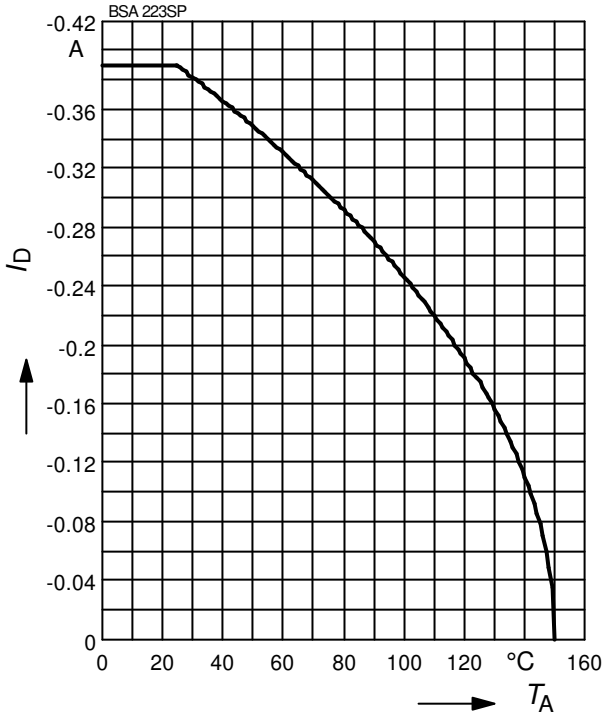
$P_{tot} = f(T_A)$



2 Drain current

$I_D = f(T_A)$

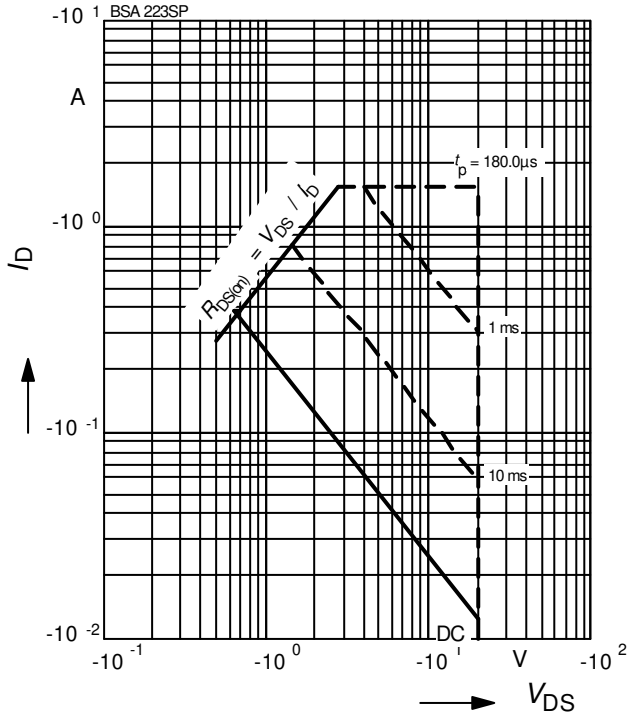
parameter: $|V_{GS}| \geq 4.5$ V



3 Safe operating area

$I_D = f(V_{DS})$

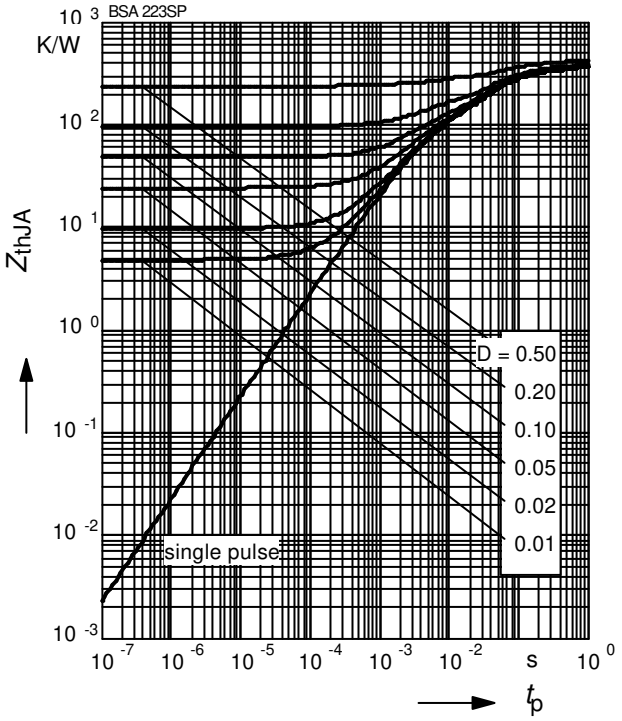
parameter : $D = 0$, $T_A = 25$ °C



4 Transient thermal impedance

$Z_{thJA} = f(t_p)$

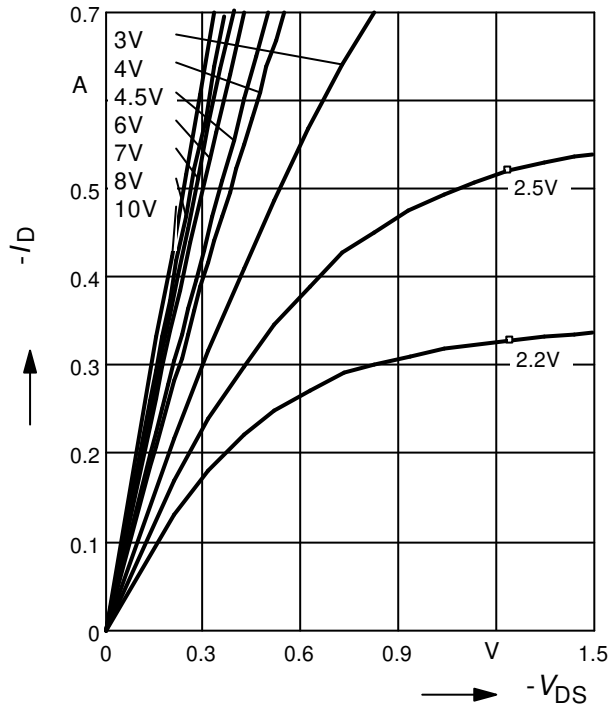
parameter : $D = t_p/T$



5 Typ. output characteristic

$I_D = f(V_{DS})$

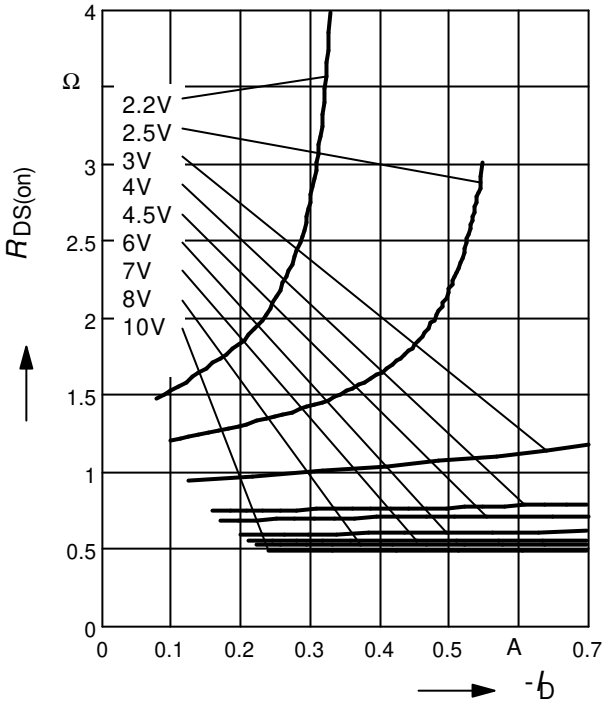
parameter: T_j =25°C



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

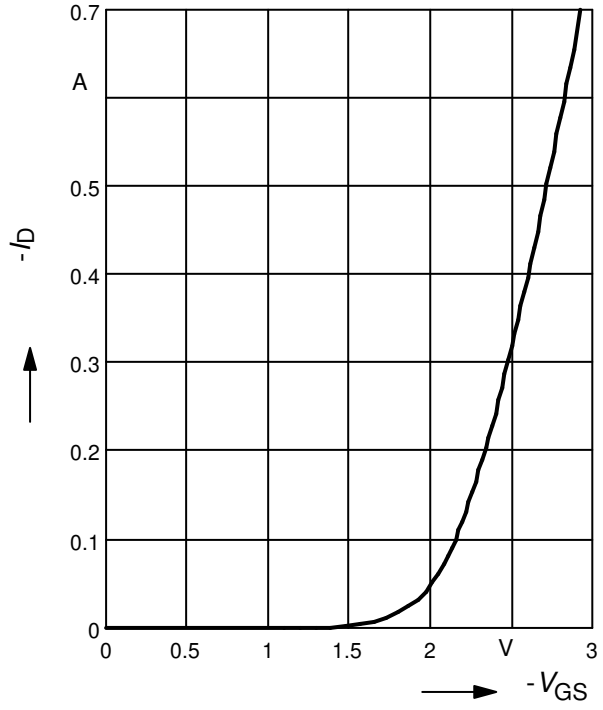
parameter: V_{GS}, T_j = 25 °C



7 Typ. transfer characteristics

$I_D = f(V_{GS})$; $|V_{DS}| \geq 2 \times |I_D| \times R_{DS(on)max}$

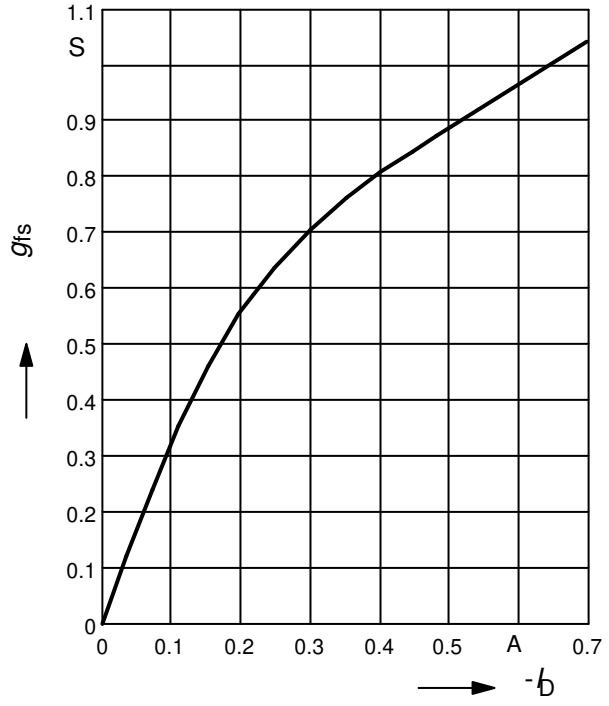
parameter: T_j = 25 °C



8 Typ. forward transconductance

$g_{fs} = f(I_D)$

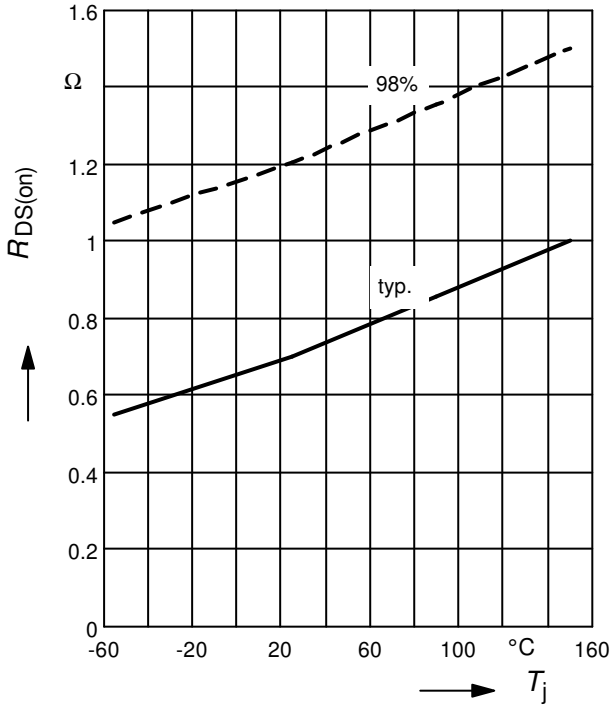
parameter: T_j = 25 °C



9 Drain-source on-resistance

$R_{DS(on)} = f(T_j)$

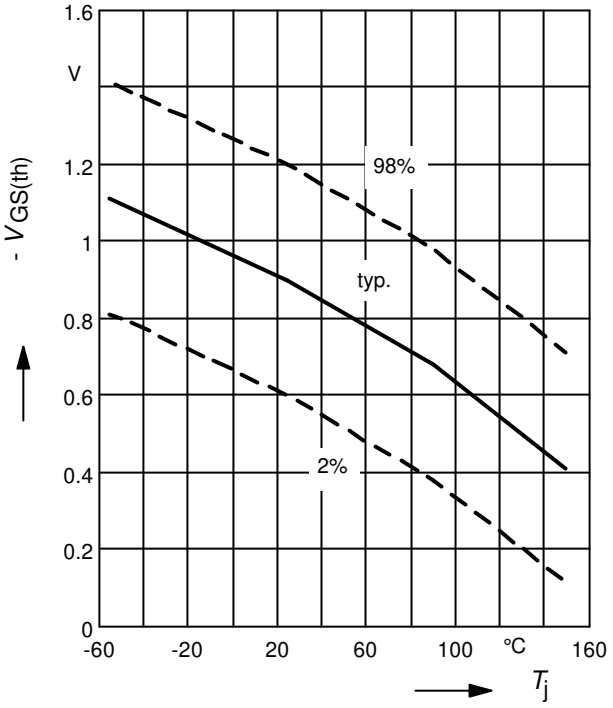
parameter: I_D = -0.39 A, V_{GS} = -4.5 V



10 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j)$

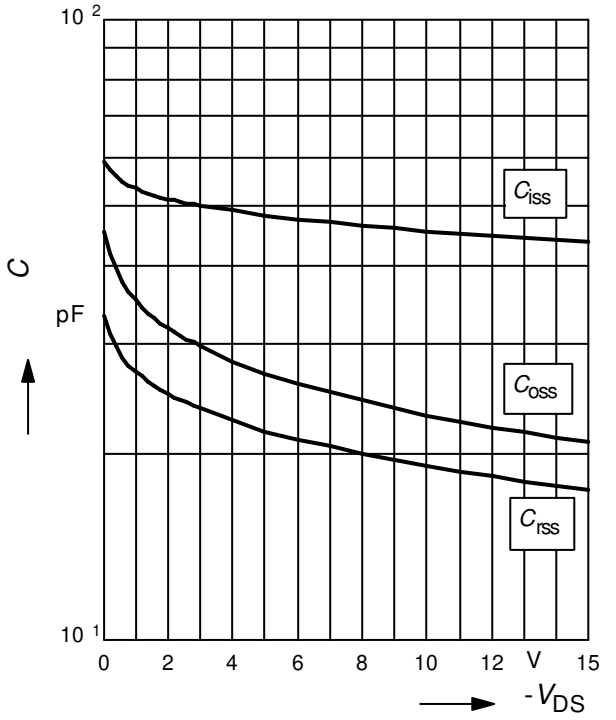
parameter: $V_{GS} = V_{DS}$



11 Typ. capacitances

$C = f(V_{DS})$

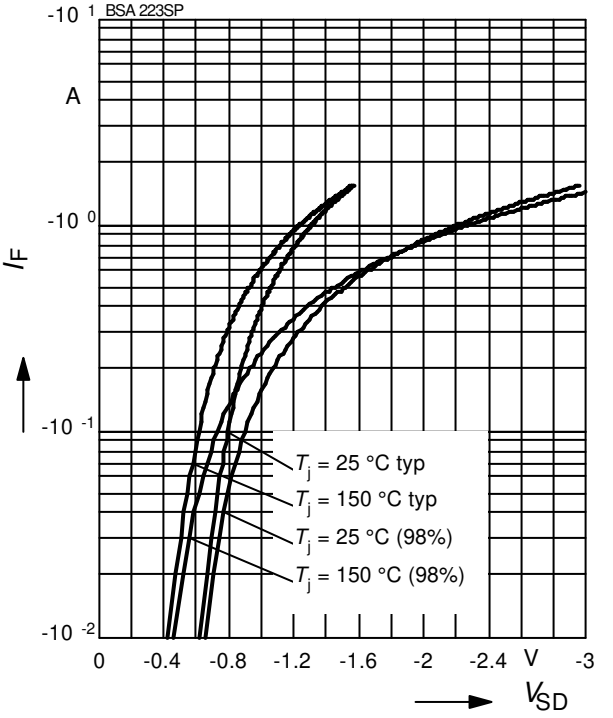
parameter: V_{GS}=0, f=1 MHz, T_j = 25 °C



12 Forward character. of reverse diode

$I_F = f(V_{SD})$

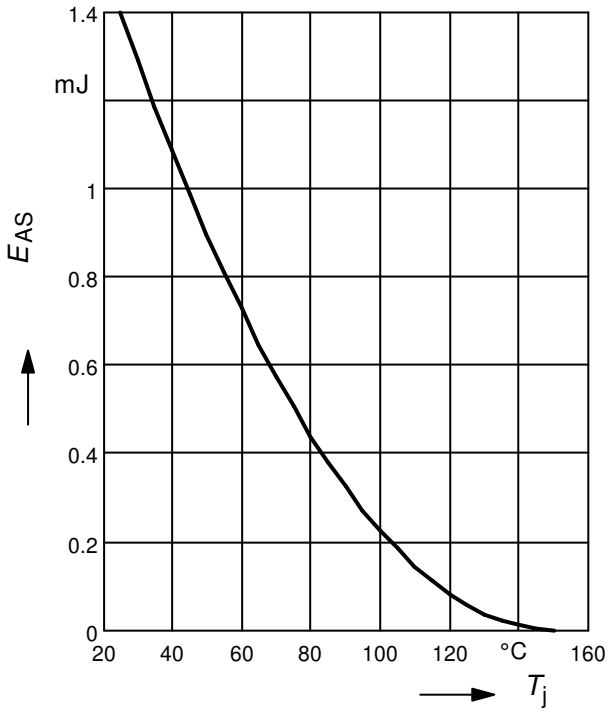
parameter: T_j = 25 °C



13 Typ. avalanche energy

$E_{AS} = f(T_j)$, par.: I_D = -0.39 A

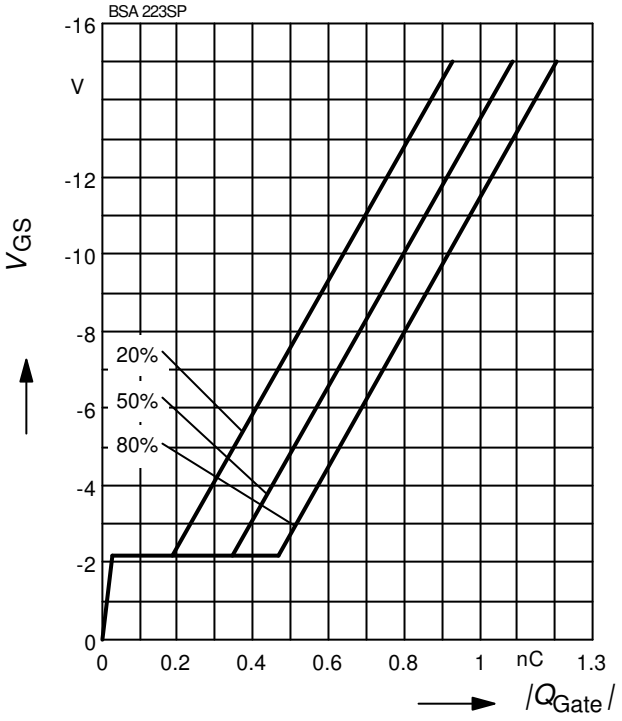
V_{DD} = -10 V, R_{GS} = 25 Ω



14 Typ. gate charge

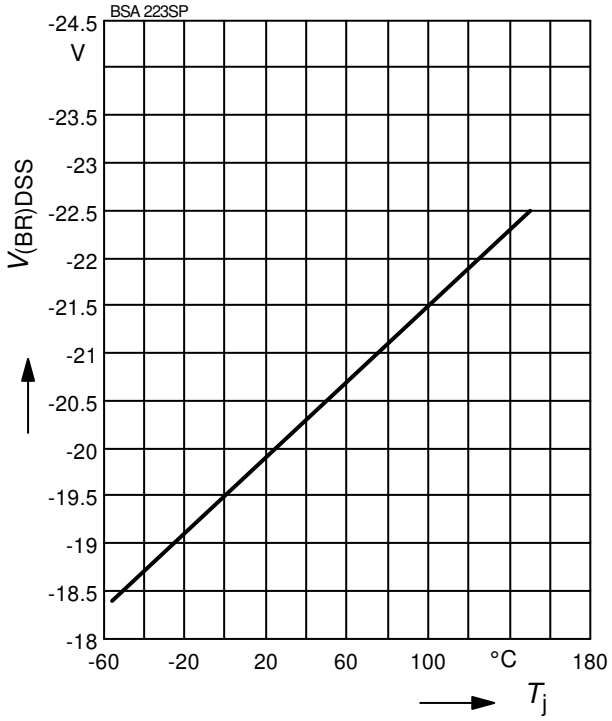
$V_{GS} = f\ (Q_{Gate})$

parameter: I_D = -0.39 A pulsed, T_j = 25 °C



15 Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$



Published by
Infineon Technologies AG,
Bereichs Kommunikation
St.-Martin-Strasse 53,
D-81541 München

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